

Curriculum Vitae

I. Personal Identity

Name : Lilik Hasanah
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II. Education

Institution	Title	Year	Specific Major
ITB (S1)	Bachelor of Science(S.Si) GPA: 3.47 (Cum Laude)	1999	Physics of Electronic Materials and Instrumentation
ITB (S2)	Master of Science (M.Si.) GPA: 3.78	2001	Physics of Electronic Materials
ITB (S3)	Doctor (Dr) (Cum Laude)	2008	Physics of Electronic Materials

III. Publication

No	Title	Year	Journal
1	Hasanah, L., dan Khairurrijal (2009) : Perhitungan Arus Terobosan pada Transistor Dwikutub Sambungan Hetero Si/Si _{1-x} Ge _x /Si Anisotropik dengan Menggunakan Metode Matriks Transfer	2009	<i>Indonesian Journal of Materials Science</i> , 287-291
2	Hasanah, L., Sukirno dan Khairurrijal (2009) : Pengaruh Regangan Si/Si _{1-x} Ge _x terhadap Arus Terobosan pada Transistor Dwikutub Sambungan Hetero Si(110)/Si _{0.5} Ge _{0.5} /Si(110) Anisotropik	2009	ISTEK UIN
3	Hasanah, L., Abdullah, M., Sukirno, Winata, T. and Khairurrijal (2008) : Model of Tunneling Current in an Anisotropic Si/Si _{1-x} Ge _x /Si Heterostructure with Nanometer-thick Barrier Including Effect of Parallel-Perpendicular Kinetic Energy Coupling	2008	<i>Semicond. Sci. and Technol.</i> , 23, 125024.
4	Hasanah, L., Abdullah, M., Sukirno, Winata, T. and Khairurrijal (2008) : Pengaruh Kecepatan Elektron terhadap Arus Terobosan pada Heterostruktur Anisotropik Si/Si _{1-x} Ge _x /Si	2008	<i>Journal Matematika dan Sains</i>
5	Hasanah, L., Suryamas, A. B., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : Electron Transmittance through a Heterostructure on Anisotropic Materials using the Airy Function and the Matrix Method	2007	<i>Indonesian Journal of Physics</i> , 17, 95-101
6	Hasanah, L., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : An Improved Analytical Method Based on Airy Function Approach to Calculate Electron Direct Transmittance in Anisotropic Heterostructure with Bias Voltage	2006	<i>Indonesian Journal of Physics</i> , 17, 77-81
7	Hasanah, L., Khairurrijal, Abdullah, M., Winata, T. and Sukirno: Transmittance of an Electron through a Heterostructure Nanometer-thick Trapezoidal Barrier Grown on an Anisotropic Material for Energy Higher Than Potential Barrier	2006	<i>9th International Conference on Quality in Research (QIR) Proceeding</i> , ICE 07, 1-4

8	Hasanah, L., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : Transmittansi Elektron pada Heterostruktur Anisotropik Si(110)/Si _{0.7} Ge _{0.3} /Si(110) dengan Tegangan Panjar	2006	<i>Prosiding Seminar Nasional Tenaga Listrik dan Mekatronik, AST-02, 7-12</i>
9	Hasanah, L., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : Electron Transmittance at Si(110)/Si _{0.5} Ge _{0.5} /Si(110) Anisotropic Heterostructure with Bias Voltage for Incident Energy Lower than Potential Barrier	2006	<i>Proceeding of the International Conference on Mathematics and Natural Sciences (ICMNS), 949-953</i>
10	Hasanah, L., Noor, F. A., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : Transmission Coefficient of an Electron through a Heterostructure with Nanometer-Thick Trapezoidal Barrier Grown on an Anisotropic Material	2006	<i>Proceeding ITB Sains & Teknologi, 38, 41-50</i>
11	Hasanah, L., Noor, F. A., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : Koefisien Transmisi Elektron yang Melalui Penghalang dengan Ketebalan Nanometer pada Heterostruktur Anisotropik yang diberi Tegangan Panjar	2005	<i>Proceeding Kentingan Physics Forum (KPI), 152-154</i>
12	Hasanah, L., Khairurrijal, Abdullah, M., Winata, T. and Sukirno : Tunneling Time and Transmission Coefficient of An Electron Tunneling Through A Nanometer-Thick Square Barrier in an Anisotropic Heterostructure	2005	<i>Proceeding International Conference Applied Mathematics (ICAM05), CP14</i>
13	Hasanah, L., Suryamas, A. B., Khairurrijal, Winata, T. and Sukirno : Simulation of Direct Tunneling Current in Metal/Gd ₂ O ₃ /n-GaN Devices with Nanometer-Thick Gd ₂ O ₃ Layers by Using Self-Consistent Solution of Schrödinger-Poisson Equation, Proceeding International Conference on Instrumentation	2005	<i>Proceeding International Conference on Instrumentation, Communication, and Information Technology (ICICI), 307-310</i>
14	Noor, F. A., Tobing, H. L. Hasanah, L., Abdullah, M. and Khairurrijal : Direct Tunneling Time of an Electron through a Nanometer Thick Trapezoidal Potential Barrier	2005	<i>Proceeding Kentingan Physics Forum (KPI), 121-123</i>

15	Noor, F. A., Tobing, H. L., Nanang, Hasanah, L. , Abdullah, M. and Khairurrijal, "Stationary-Phase Electron Direct Tunneling through an Anisotropic Heterostructure with Nanometer-Thick Trapezoidal Potential Barrier	2004	<i>Proceeding of Asian Physics Symposium, 302-306</i>
16	Sukirno, SZ Bisri, L. Hasanah , Mursal, Ida Usman, AB Suryamas, TA Edison : Low Temperature Carbon Nanotube Fabrication using Very High Frequency-Plasma Enhanced Chemical Vapour Deposition Method	2006	<i>ICSE 2006 International Conference on Semiconductor Electronics, e-Journal IEEE Xplore, 155-159</i>
17	Sukirno, SZ Bisri, Irmelia, L. Hasanah , AB Suryamas, Mursal, Ida dan Usman : Comparison of Electronic Transport Parameter of CNT (10,10)/CNT(17,0) and CNT (5,5)/CNT(8,0) Carbon Nanotube Metal-Semiconductor On-Tube Heterojunction	2006	<i>ICSE 2006 International Conference on Semiconductor Electronics, e-Journal IEEE Xplore, 267-271</i>
18	Bisri. S. Z., Suryamas, A. B., Hasanah, L. and Sukirno : Simulation of Carbon Nanotube on-Tube Metal Semiconductur Heterojunction Electronic Properties	2005	<i>Indonesian Journal of Physics, 17, 21-29</i>
19	Bisri. S. Z., Hasanah, L. and Sukirno : Charge Distribution and Potential Profile in Nanometer Metallic Carbon Nanotubes-Semiconducting Carbon Nanotube Heterojunction	2005	<i>Proceeding of Asian Physics Symposium</i>
20	Sari, R. S, Bisri. S. Z., Hasanah, L. and Sukirno : Carbon Nanotube Fabrication Attempt: Our Recent Progress	2005	<i>Proceeding of 6th International Seminar on Microscopy and Microanalysis: "Nanotechnology and Its Application</i>

IV. Research

1. Mekanisme Transport Listrik pada Detektor Ultraviolet Berbasis Semikonduktor GaN dengan Struktur Metal-Semikonduktor-Metal, Hibah Fundamental, 2009
2. Fabrikasi Lapisan Tipis Nd-CeO₂ untuk SOFC menggunakan teknik PLAD, Hibah Pascasarjana, 2005-2006
3. Fabrikasi, Simulasi dan Karakterisasi CNT II, Riset Unggulan Fakultas FMIPA ITB, 2006

4. Fabrikasi, Simulasi dan Karakterisasi CNT, Riset Unggulan Fakultas FMIPA ITB, 2005
5. Diagnosa Kesulitan Mahasiswa dalam Perkuliahan Fisika Statistik ditinjau dalam Hal Kemampuan Matematika dan Fisikanya Penelitian Mandiri Jurusan Fisika FPMIPA UPI, Januari – April 2003
6. Penumbuhan Film Tipis GaSb diatas Substrat GaAs dengan menggunakan Reaktor MOCVD Vertikal, Hibah Bersaing, Jurusan Fisika Laboratorium Fismatel ITB, 2000 – 2001

V. Professional Experience

Jurusan Fisika FPMIPA Universitas Pendidikan Indonesia (UPI) Bandung

- Lecturer (2001 – now)

Institut Agama Islam Negri Sunan Gunung Djati Bandung

- Lecturer at Jurusan Fisika Fakultas Tarbiyah (2002 – now)
- Lecturer at Jurusan Fisika dan Teknik Elektro Fakultas Sains dan Teknologi (2008 – now)

Institut Teknologi Telekomunikasi (IT Telkom) Bandung

- Lecturer (January 2009-now)

Bandung, 26 Maret 2010

Dr. Lilik Hasanah, S.Si, M Si